Sheet 1 of 1

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
SR		10-141487	05/1998	JP			Abstract	
SR		8-32040	02/1996	JP			Abstract	
SR		10-125925	05/1998	JP			Abstract	
SR		8-222705	08/1996	JP			Abstract	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

SR		A. YOSHINO, et al., IEEE Intl. SOI Conference, 10/1995, "HIGHSPEED PERFORMANCE OF 0.35 Mm CMOS Gates Fabriccated...", p. 4

*Examiner: Shousung Lee — Date Considered: 2/14/02

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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